

2SB560

TO-92MOD Transistor (PNP)



1. EMITTER
2. COLLECTOR
3. BASE

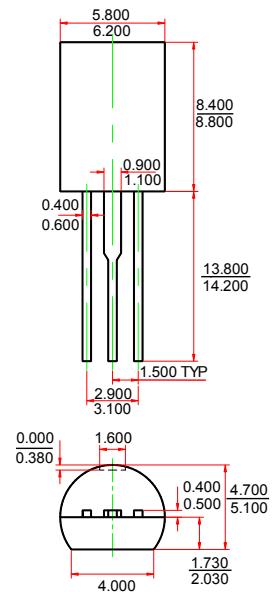
Features

- ✧ High reverse voltage
- ✧ Low saturation voltage
- ✧ Suitable universal AF power amplifier use

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.7	A
P_C	Collector Power Dissipation	900	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

TO-92MOD



Dimensions in inches and (millimeters)

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu\text{A}$, $I_E = 0$	-100		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{mA}$, $I_B = 0$	-80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}$, $I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -20 \text{V}$, $I_E = 0$		-1	μA
Collector cut-off current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_B = 0$		-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}$, $I_C = -50\text{mA}$	60	560	
	$h_{FE(2)}$	$V_{CE} = -5\text{V}$, $I_C = -500\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{mA}$, $I_B = -50\text{mA}$	-0.3	-0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{mA}$, $I_B = -50\text{mA}$	-0.85	-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}$, $I_C = -50\text{mA}$		100	MHz
Out capacitance	C_{ob}	$V_{CB} = -10 \text{V}$, $f = 1\text{MHz}$		15	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F	G
Range	60 - 120	100 - 200	160 - 320	280 - 560

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Typical Characteristics

